



100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) MAX	I _D MAX T _C = +25°C
100V	32mΩ @ V _{GS} = 10V	17A
	50mΩ @ V _{GS} = 4.5V	13A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

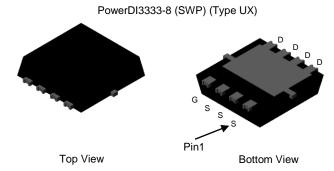
- Backlighting
- Power Management Functions
- DC-DC Converters

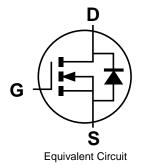
Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.072 grams (Approximate)





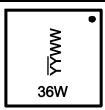
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H032LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape and Reel
DMT10H032LFVW-13	PowerDI3333-8 (SWP) (Type LIX)	3.000/Tape and Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information





Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage	Vgss	±20	V	
	T _C = +25°C	1-	17	- A
Continuous Drain Current (Note 7) V _{GS} = 10V	Tc = +70°C	ID	13	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	68	А	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	17	А	
Pulsed Body Diode Forward Current (Note 8)	Ism	68	Α	
Avalanche Current, L = 0.3mH (Note 8)		I _{AS}	13	Α
Avalanche Energy, L = 0.3mH (Note 8)		Eas	25.3	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	92	°C/W
Total Power Dissipation (Note 6)		PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		RθJA	49	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	8.9	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

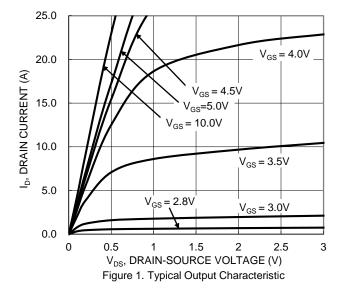
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	1.3	l	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		22	32	mΩ	Vgs = 10V, ID = 10A	
Static Drain-Source On-Resistance	RDS(ON)	_	30	50	11177	$V_{GS} = 4.5V, I_D = 5A$	
Diode Forward Voltage	V _{SD}	_	0.8	1	V	Vgs = 0V, Is = 6A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	ı	683	_	рF	50111	
Output Capacitance	Coss	1	165	_	pF	$V_{DS} = 50V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	6.9	_	pF	11 = 110102	
Gate Resistance	Rg		1.2	_	Ω	Ω V _{DS} = 0V, V _{GS} = 0V, f = 1MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.3	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	11.9	_	nC	\/	
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{DS} = 50V, I_{D} = 6A$	
Gate-Drain Charge	Q _{gd}		3.1	_	nC	1	
Turn-On Delay Time	td(ON)		4.1	_	ns	$V_{DS} = 50V, R_{L} = 5.85\Omega$	
Turn-On Rise Time	t _R		4.5	_	ns		
Turn-Off Delay Time	tD(OFF)		12.5	_	ns	$V_{GS} = 10V, R_g = 3\Omega$	
Turn-Off Fall Time	tF		9.3	_	ns	1	
Reverse Recovery Time	t _{RR}	-	31.5	_	ns		
Reverse Recovery Charge	Qrr	-	94.6	_	nC	I _F = 6A, di/dt = 500A/μs	

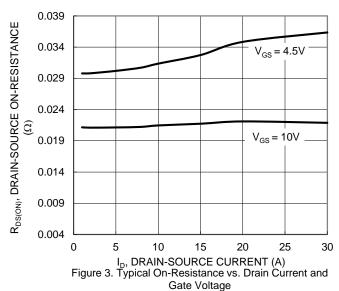
Notes: 5. Device i

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_{J} = +25^{\circ}C$.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

DMT10H032LFVW Document number: DS41982 Rev. 2 - 2







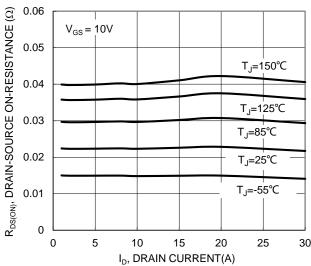


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

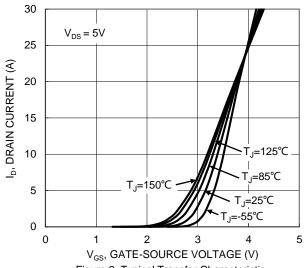


Figure 2. Typical Transfer Characteristic

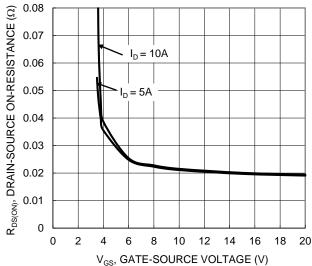


Figure 4. Typical Transfer Characteristic

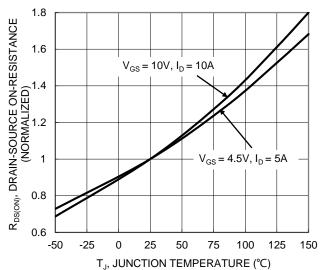
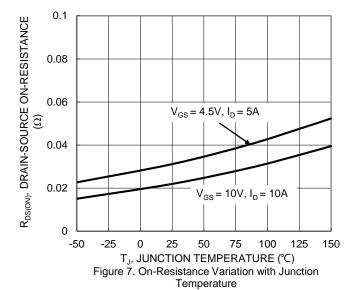
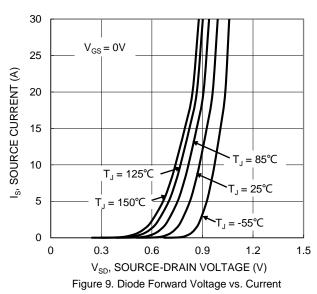
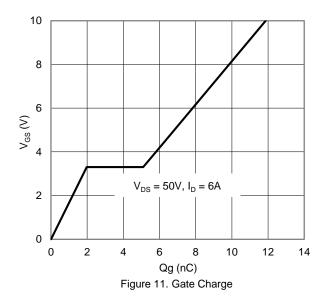


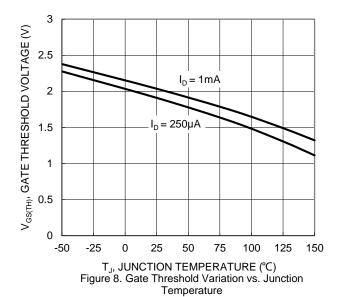
Figure 6. On-Resistance Variation with Junction Temperature

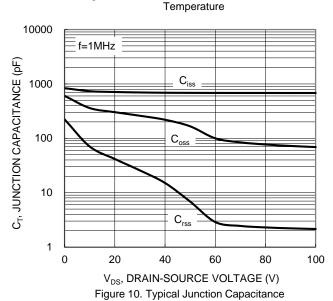


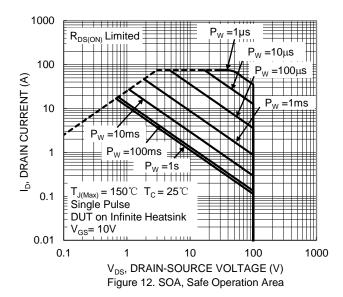














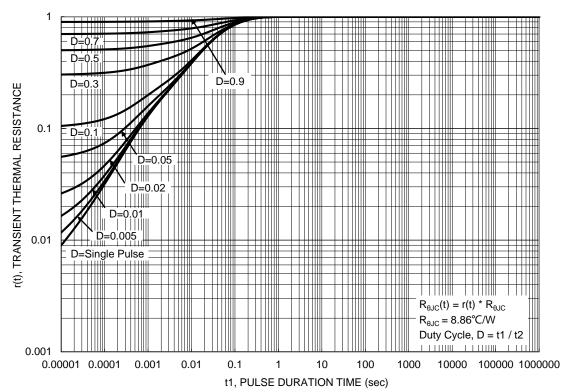


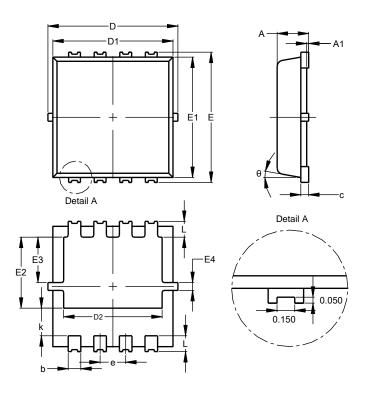
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

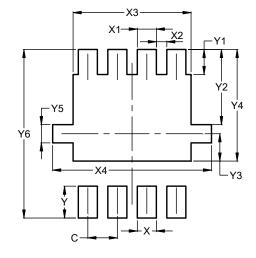


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min Max Typ				
Α	0.75	0.85	0.80		
A1	0.00	0.05	-		
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е			0.65		
k	0.50	0.90	0.70		
٦	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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